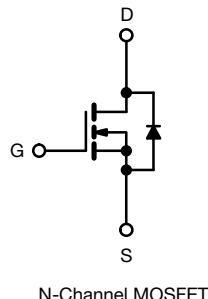
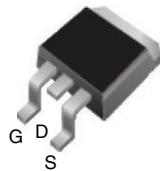


Power MOSFET

D²PAK (TO-263)


PRODUCT SUMMARY

V_{DS} (V)	60	
$R_{DS(on)}$ (Ω)	$V_{GS} = 5.0$ V	0.028
Q_g (Max.) (nC)	66	
Q_{gs} (nC)	12	
Q_{gd} (nC)	43	
Configuration	Single	

FEATURES

- Surface-mount
- Available in tape and reel
- Dynamic dV/dt rating
- Logic-level gate drive
- $R_{DS(on)}$ specified at $V_{GS} = 4$ V and 5 V
- 175 °C operating temperature
- Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS*
Available
HALOGEN
FREE
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D²PAK (TO-263) is a surface-mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface-mount package. The D²PAK (TO-263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

ORDERING INFORMATION

Package	D ² PAK (TO-263)		D ² PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHLZ44S-GE3		SiHLZ44STRR-GE3 ^a
Lead (Pb)-free	IRLZ44SPbF		IRLZ44STRRPbF ^a

Note

a. See device orientation

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage		± 10	
Continuous Drain Current ^f	I_D	50	A
Continuous Drain Current		36	
Pulsed Drain Current ^a	I_{DM}	200	
Linear Derating Factor		1.0	W/°C
Linear Derating Factor (PCB Mount) ^e		0.025	
Single Pulse Avalanche Energy ^b	E_{AS}	400	mJ
Maximum Power Dissipation	P_D	150	W
Maximum Power Dissipation (PCB Mount) ^e		3.7	
Peak Diode Recovery dV/dt ^c	dV/dt	4.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) ^d	For 10 s	300 ^d	

Notes

b. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

c. $V_{DD} = 25$ V, starting $T_J = 25$ °C, $L = 179$ μ H, $R_g = 25$ Ω , $I_{AS} = 51$ A (see fig. 12)

d. $I_{SD} \leq 51$ A, $dI/dt \leq 250$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C

e. 1.6 mm from case

f. When mounted on 1" square PCB (FR-4 or G-10 material)

g. Current limited by the package, (die current = 51 A)

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	$^{\circ}\text{C}/\text{W}$
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

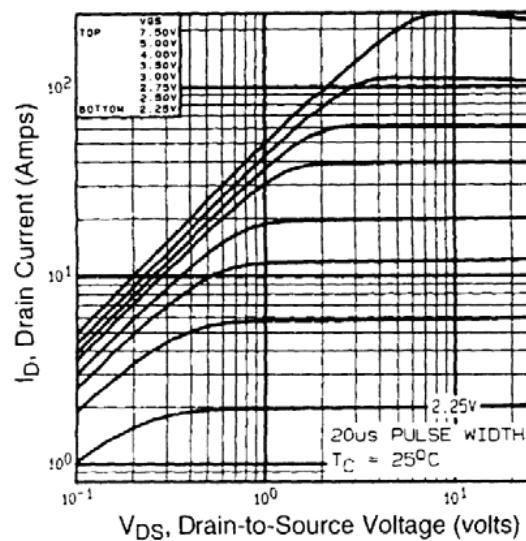
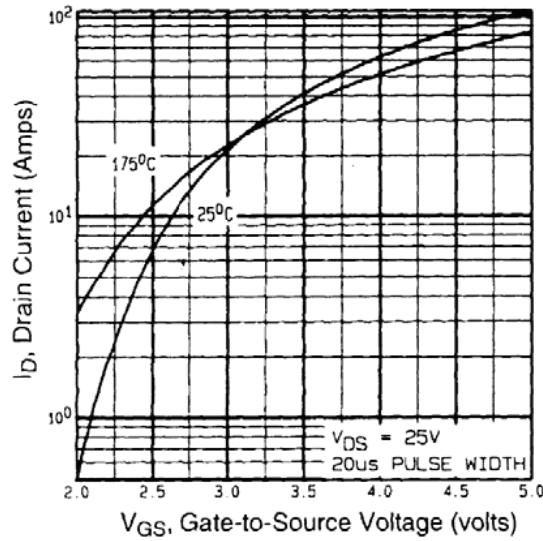
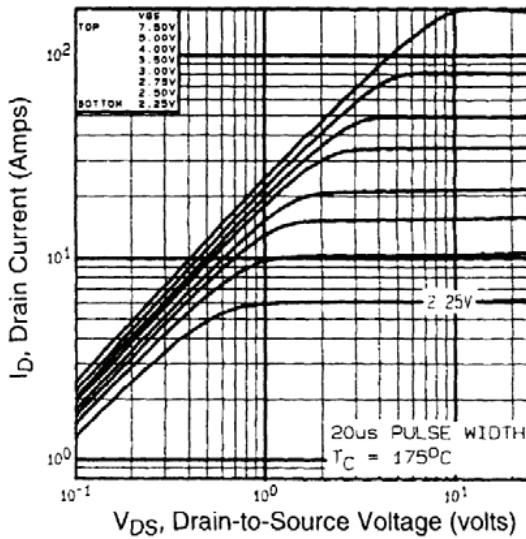
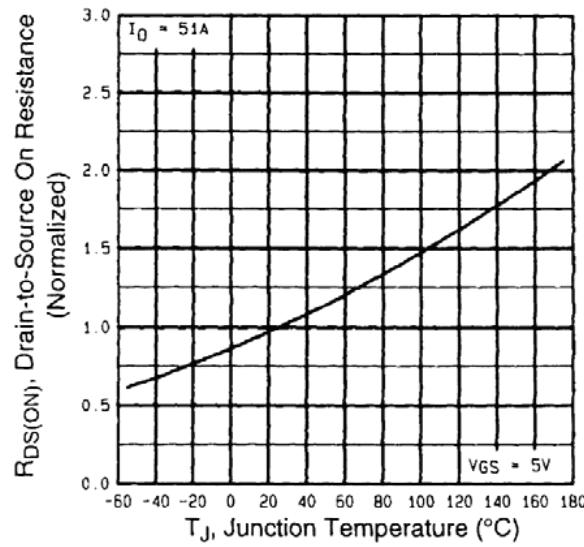
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250 \mu\text{A}$		60	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 1 \text{ mA}$		-	0.070	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		1.0	-	2.0	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 10 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$		-	-	25	μA	
		$V_{DS} = 48 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 150 \text{ }^{\circ}\text{C}$		-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 5.0 \text{ V}$	$I_D = 31 \text{ A}^b$	-	-	0.028	Ω	
		$V_{GS} = 4.0 \text{ V}$	$I_D = 25 \text{ A}^b$	-	-	0.039		
Forward Transconductance	g_{fs}	$V_{DS} = 25 \text{ V}$, $I_D = 31 \text{ A}^b$		23	-	-	S	
Dynamic								
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1.0 \text{ MHz}$, see fig. 5		-	3300	-	pF	
Output Capacitance	C_{oss}			-	1200	-		
Reverse Transfer Capacitance	C_{rss}			-	200	-		
Total Gate Charge	Q_g	$V_{GS} = 5.0 \text{ V}$	$I_D = 51 \text{ A}$, $V_{DS} = 48 \text{ V}$, see fig. 6 and 13 ^b	-	-	66	nC	
Gate-Source Charge	Q_{gs}			-	-	12		
Gate-Drain Charge	Q_{gd}			-	-	43		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30 \text{ V}$, $I_D = 51 \text{ A}$, $R_g = 4.6 \Omega$, $R_D = 0.56 \Omega$, see fig. 10 ^b		-	17	-	ns	
Rise Time	t_r			-	230	-		
Turn-Off Delay Time	$t_{d(off)}$			-	42	-		
Fall Time	t_f			-	110	-		
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH	
Internal Source Inductance	L_S			-	7.5	-		
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	50 ^c	A	
Pulsed Diode Forward Current ^a	I_{SM}			-	-	200		
Body Diode Voltage	V_{SD}	$T_J = 25 \text{ }^{\circ}\text{C}$, $I_S = 51 \text{ A}$, $V_{GS} = 0 \text{ V}^b$		-	-	2.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25 \text{ }^{\circ}\text{C}$, $I_F = 51 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}^b$		-	130	180	ns	
Body Diode Reverse Recovery Charge	Q_{rr}			-	0.84	1.3	μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)						

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width $\leq 300 \mu\text{s}$; duty cycle $\leq 2 \%$

c. Current limited by the package, (Die Current = 51 A)

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_c = 25\text{ }^{\circ}\text{C}$

Fig. 2 - Typical Transfer Characteristics

Fig. 1 - Typical Output Characteristics, $T_c = 150\text{ }^{\circ}\text{C}$

Fig. 3 - Normalized On-Resistance vs. Temperature

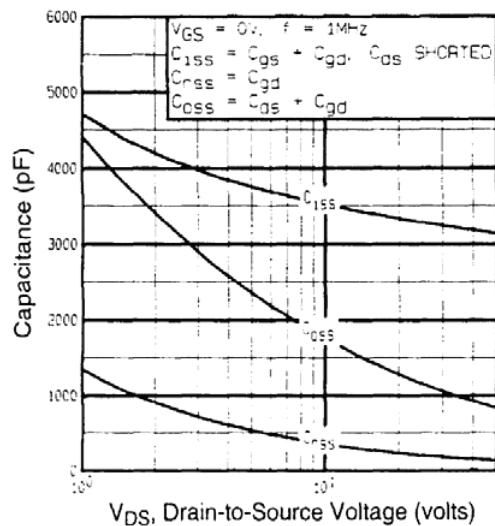


Fig. 4 - Typical Capacitance vs. Drain-to-Source Voltage

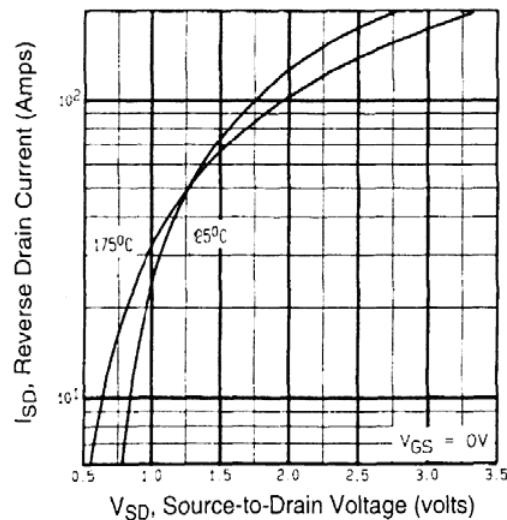


Fig. 6 - Typical Source-Drain Diode Forward Voltage

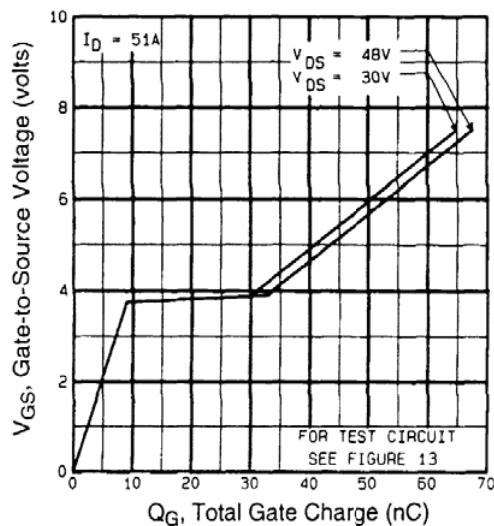


Fig. 5 - Typical Gate Charge vs. Gate-to-Source Voltage

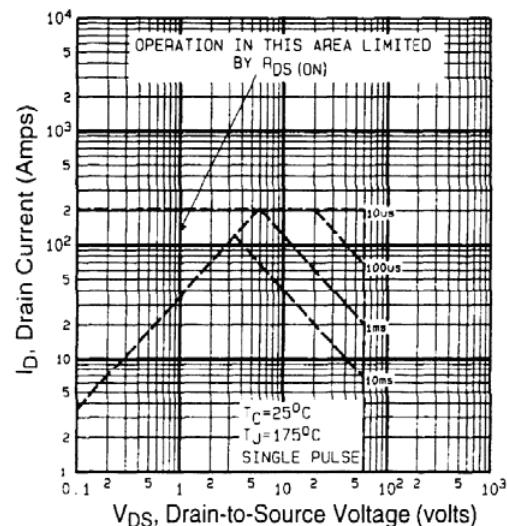


Fig. 7 - Maximum Safe Operating Area

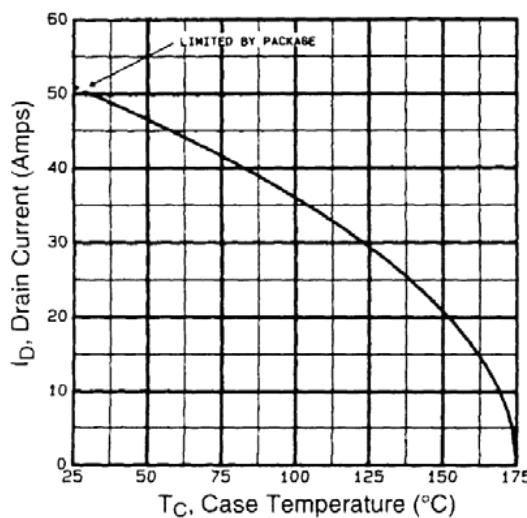


Fig. 8 - Maximum Drain Current vs. Case Temperature

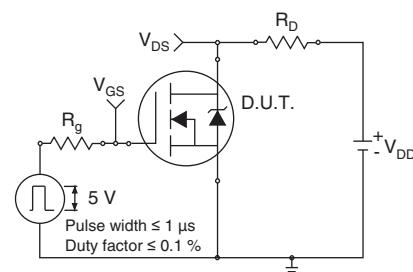


Fig. 10a - Switching Time Test Circuit

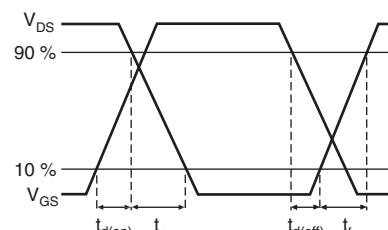


Fig. 10b - Switching Time Waveforms

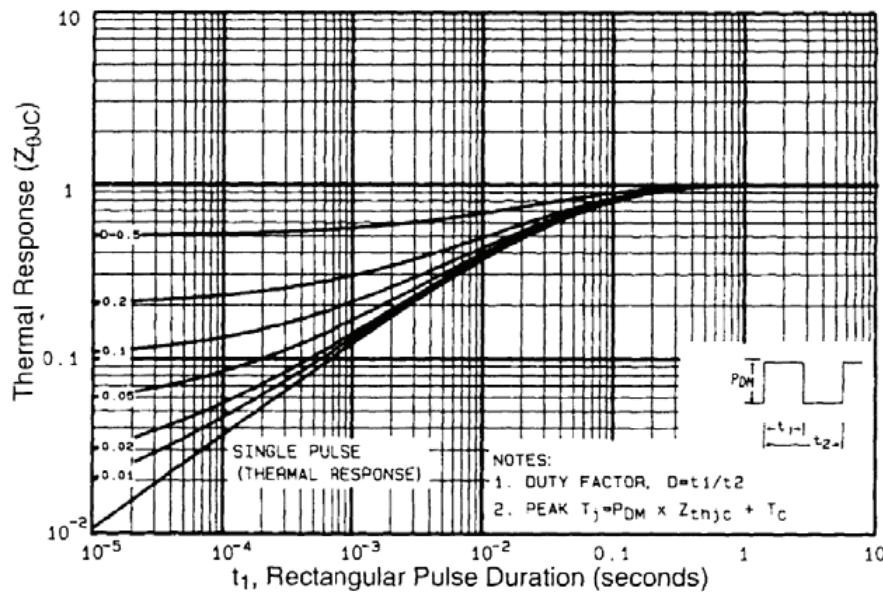


Fig. 9 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

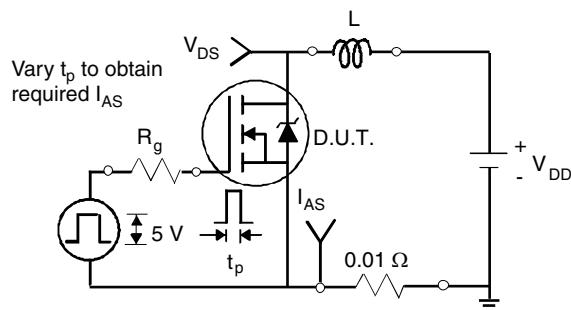


Fig. 12a - Unclamped Inductive Test Circuit

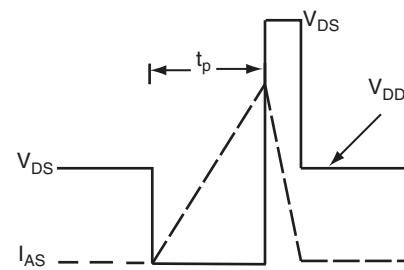


Fig. 12b - Unclamped Inductive Waveforms

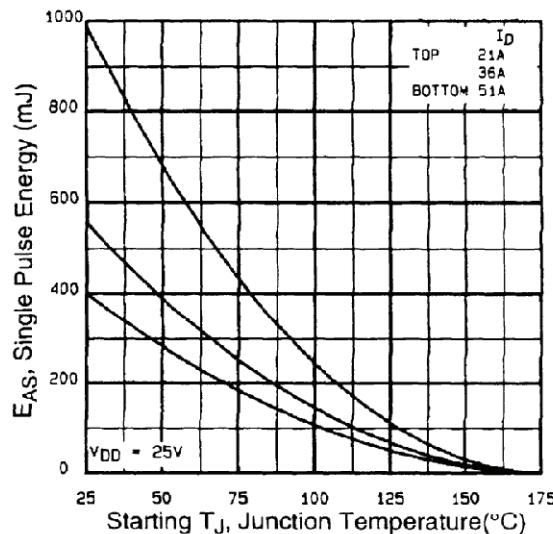


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

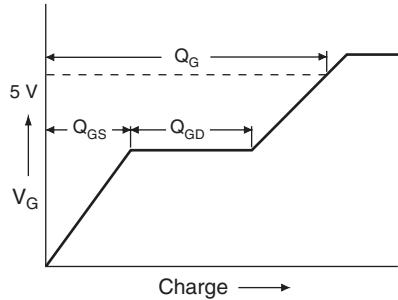


Fig. 13a - Basic Gate Charge Waveform

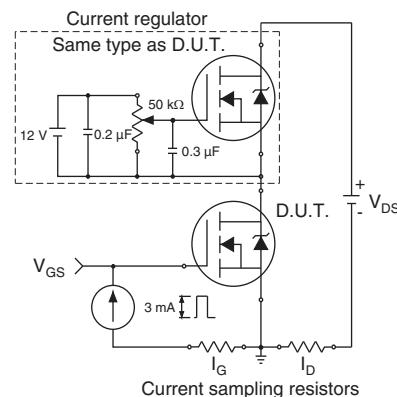


Fig. 13b - Gate Charge Test Circuit

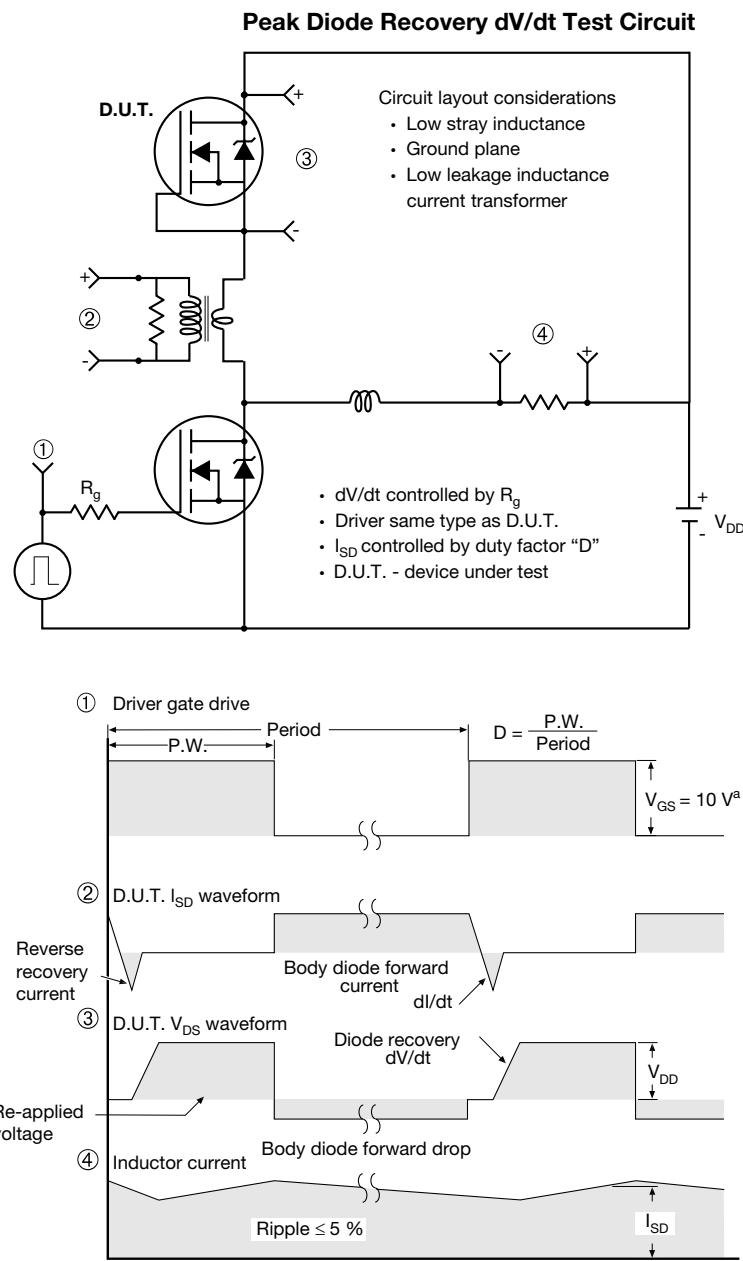
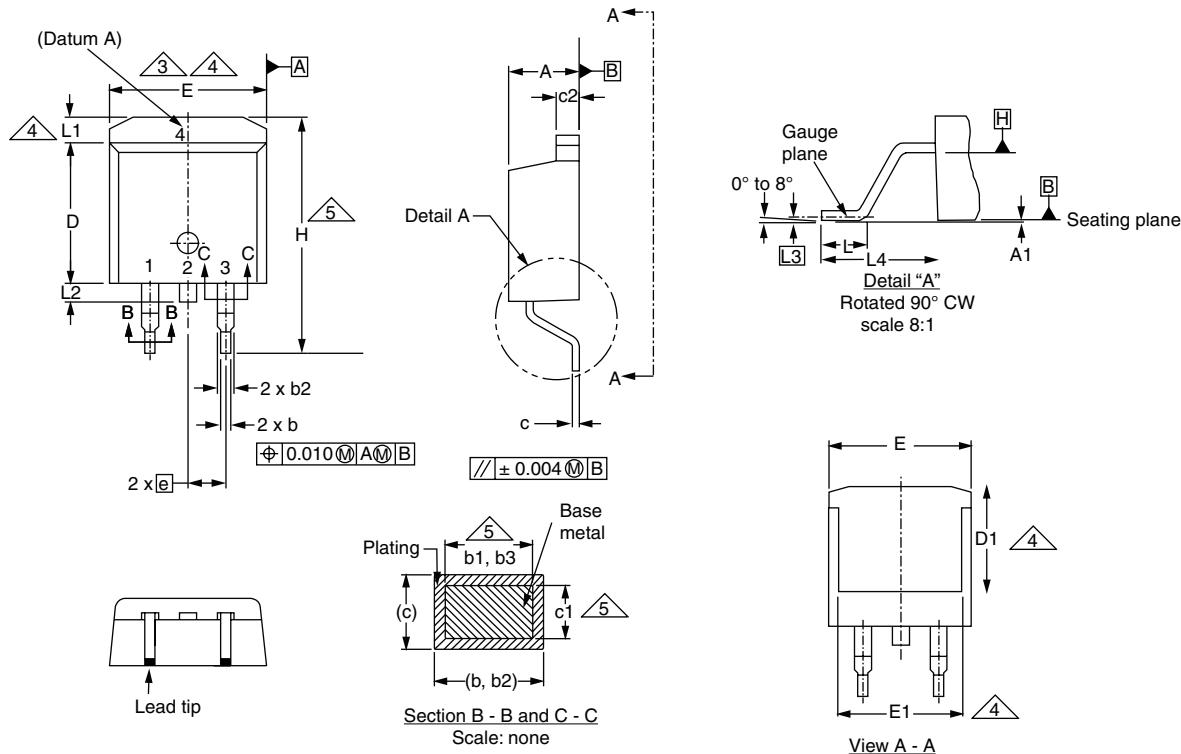


Fig. 10 - For N-Channel

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TO-263AB (HIGH VOLTAGE)



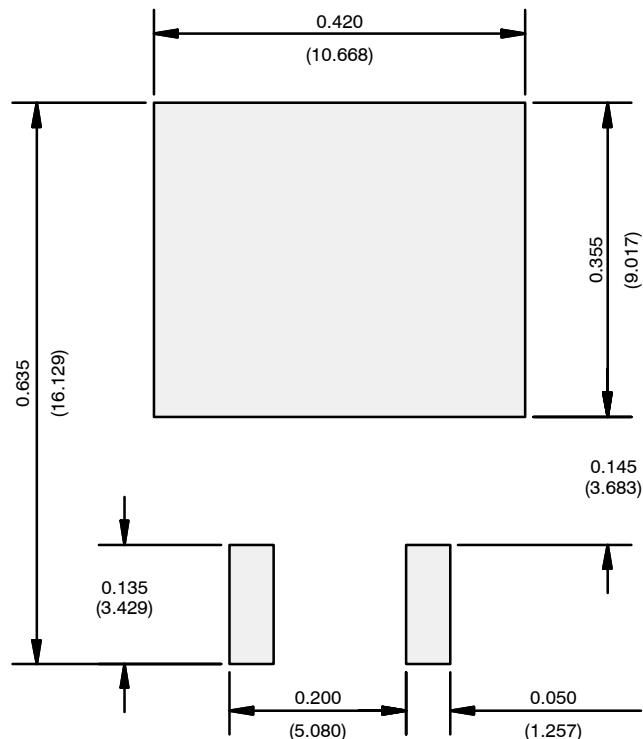
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead

Recommended Minimum Pads
Dimensions in Inches/(mm)

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